

NX6510GH

Data Sheet

LASER DIODE

1 550 nm InGaAsP MQW-DFB LASER DIODE

FOR 1.25 Gb/s FTTH P2P AND OC-48 IR-2

R08DS0051EJ0100

Rev.1.00

Jan 19, 2012

DESCRIPTION

The NX6510GH is a 1 550 nm Multiple Quantum Well (MQW) structured Distributed Feed-Back (DFB) laser diode with InGaAs monitor PIN-PD.

APPLICATIONS

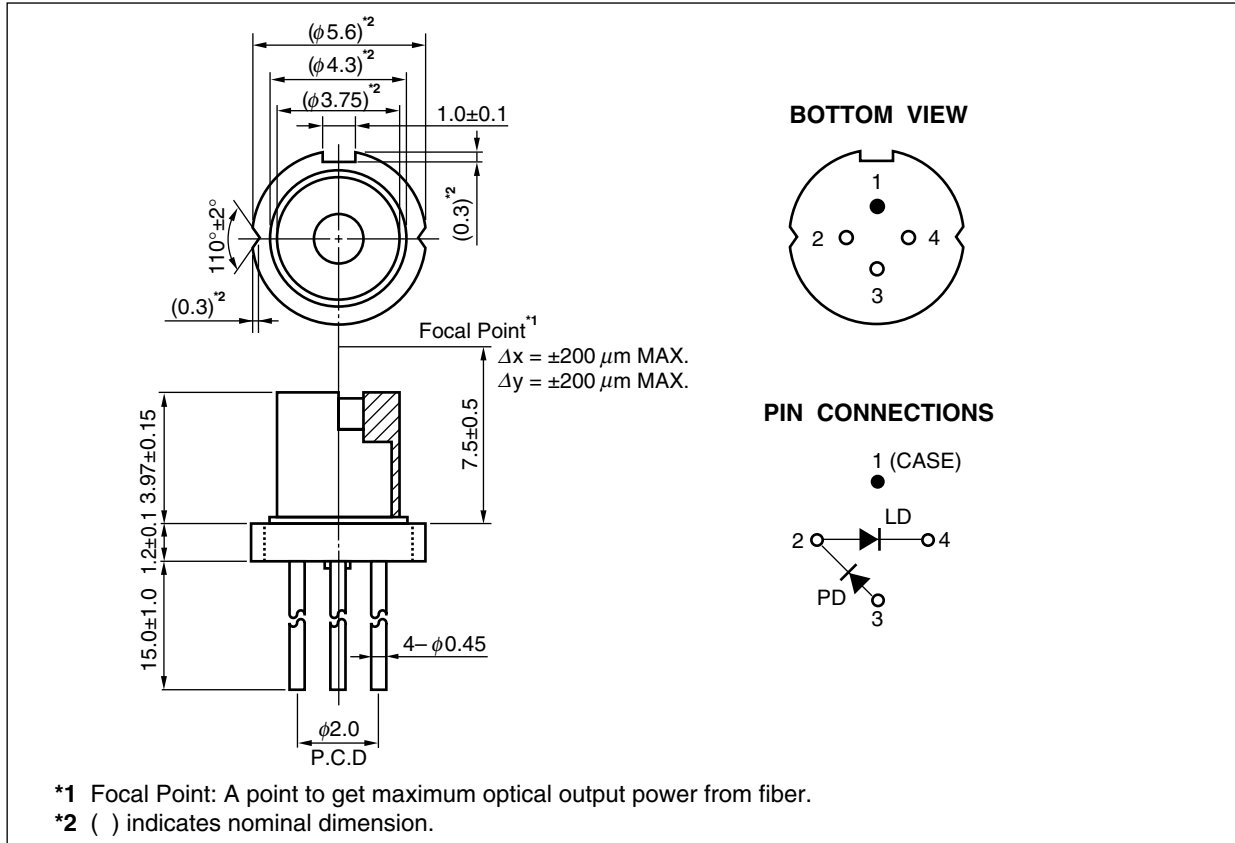
- 1.25 Gb/s FTTH P2P
- OC-48 IR-2

FEATURES

- | | |
|------------------------------------|---|
| • Optical output power | $P_O = 5.0 \text{ mW}$ |
| • Low threshold current | $I_{th} = 10 \text{ mA}$ |
| • Differential efficiency | $\eta_d = 0.35 \text{ W/A}$ |
| • Wide operating temperature range | $T_C = -40 \text{ to } +85^\circ\text{C}$ |
| • InGaAs monitor PIN-PD | |
| • CAN package | $\phi 5.6 \text{ mm}$ |
| • Focal point | 7.5 mm |

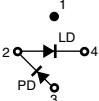


PACKAGE DIMENSIONS (UNIT: mm)



NX6510GH

ORDERING INFORMATION

Part Number	Package	Pin Connections
NX6510GH 0Z	4-pin CAN with aspherical lens cap	

- Remarks**
1. The color of lens cap might be observed differently.
 2. The hermetic test will be performed as AQL 1.0%.

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, unless otherwise specified)

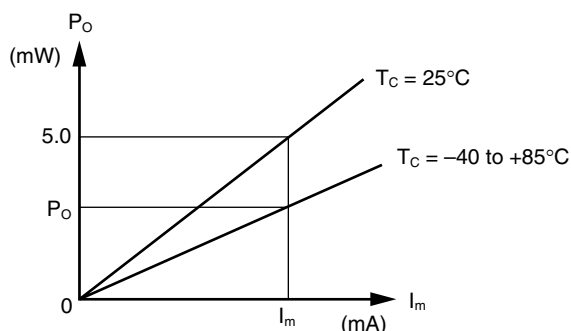
Parameter	Symbol	Ratings	Unit
Optical Output Power	P _O	10	mW
Forward Current of LD	I _F	150	mA
Reverse Voltage of LD	V _R	2.0	V
Forward Current of PD	I _F	10.0	mA
Reverse Voltage of PD	V _R	15	V
Operating Case Temperature	T _C	-40 to +85	°C
Storage Temperature	T _{stg}	-40 to +85	°C
Lead Soldering Temperature	T _{sld}	350 (3 sec.)	°C
Relative Humidity (noncondensing)	RH	85	%

ELECTRO-OPTICAL CHARACTERISTICS

(T_C = 25°C, CW, BOL, unless otherwise specified)

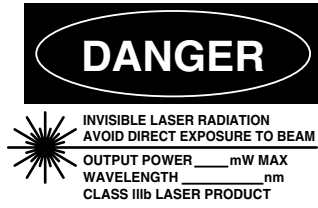
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Optical Output Power	P _O		–	5.0	–	mW
Operating Voltage	V _{op}	P _O = 5.0 mW, T _C = -40 to 85°C	–	1.1	1.6	V
Threshold Current	I _{th}		–	10	20	mA
		T _C = -40 to 85°C	–	–	50	
Differential Efficiency	η _d	P _O = 5.0 mW	0.20	0.35	–	W/A
		P _O = 5.0 mW, T _C = -40 to 85°C	0.10	–	–	W/A
Peak Emission Wavelength	λ _p	P _O = 5.0 mW, T _C = -40 to 85°C	1 530	–	1 570	nm
Side Mode Suppression Ratio	SMSR	P _O = 5.0 mW, T _C = -40 to 85°C	30	–	–	dB
Rise Time	t _r	I _b = I _{th} , 20-80% P _O = 5.0 mW	–	100	150	ps
Fall Time	t _f	I _b = I _{th} , 80-20% P _O = 5.0 mW	–	100	150	ps
Monitor Current	I _m	V _R = 1.5 V, P _O = 5.0 mW	80	–	1 200	μA
Monitor Dark Current	I _D	V _R = 5 V, T _C = -40 to 85°C	–	–	100	nA
Monitor PD Terminal Capacitance	C _t	V _R = 5 V	–	–	20	pF
Tracking Error ^{*1}	γ	T _C = -40 to 85°C, I _m = const. (@ P _O = 5.0 mW, T _C = 25°C)	-1.0	–	1.0	dB

Note: 1. Tracking Error: γ

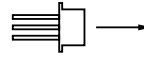


$$\gamma = \left| 10 \log \frac{P_o}{5.0} \right| \text{ [dB]}$$

SAFETY INFORMATION ON THIS PRODUCT



SEMICONDUCTOR LASER



AVOID EXPOSURE-Invisible
 Laser Radiation is emitted from
 this aperture

<p>Warning Laser Beam</p>	<p>A laser beam is emitted from this diode during operation. The laser beam, visible or invisible, directly or indirectly, may cause injury to the eye or loss of eyesight.</p> <ul style="list-style-type: none"> • Do not look directly into the laser beam. • Avoid exposure to the laser beam, any reflected or collimated beam.
<p>Caution GaAs Products</p>	<p>This product uses gallium arsenide (GaAs). GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.</p> <ul style="list-style-type: none"> • Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below. <ol style="list-style-type: none"> 1. Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials. 2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal. • Do not burn, destroy, cut, crush, or chemically dissolve the product. • Do not lick the product or in any way allow it to enter the mouth.

Revision History	NX6510GH Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Jan 19, 2012	-	First edition issued

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